EXPRESS MAIL LABEL NO. EV296621106US

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Serial No.:

Unknown

Filed:

March 10, 2004

Group Art Unit:

Unknown

Examiner:

Unknown

Applicant:

Anthony Dip, Pradip K. Roy, Sanjeev Kaushal, Allen J. Leith,

Seungho Oh, Raymond Joe

Title:

A SILICON GERMANIUM SURFACE LAYER FOR HIGH-K

DIELECTRIC INTEGRATION

Attorney Docket:

TPS-007

Cincinnati, Ohio 45202

March 10, 2004

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

INFORMATION DISCLOSURE STATEMENT

In accordance with the duty of candor and good faith imposed by 37 C.F.R. §1.56 and means of complying therewith according to 37 C.F.R. §\$1.97 and 1.98, the references listed on the attached Form PTO-1449 are called to the attention of the United States Patent and Trademark Office in connection with the above-identified patent application.

Because the requirement (37 C.F.R. §1.98(a)(2)(i)) for submitting copies of U.S. patents and published applications has been waived, copies of only the foreign cited references and other documents are enclosed herewith.

No representation is made that the cited art is the only art or that the cited art represents the best art.

The Examiner is urged to consider all of the cited documents and to make an independent evaluation of the teachings and materiality of each.

If any additional fees are necessary to complete this communication, please apply them to Deposit Account No. 23-3000.

Respectfully submitted,

WOOD, HERRON & EVANS, L.L.P.

By: Kuti Z Navo

2700 Carew Tower
441 Vine Street
Cincinnati, OH 45202
(513) 241-2324 (voice)
(513) 241-6234 (facsimile)
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	A.R	Stephen St. Onge and Mark Dupuis, <u>Innovations in Silicon Germanium Bicmos Processing</u> , Semiconductor Fabtech - 12th Edition, pp 195-199, published July, 2000.														
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